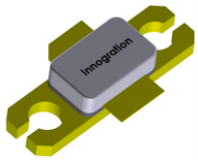
GaN 28V 70W,C band RF Power Transistor

XTAH58070GX



Description

The XTAH58070GX is a 70W internally matched, GaN HEMT, designed from 5.0 to 6.0GHz, especially 5G NR or LTE application, as well as either Pulse or CW application

There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical performance (on narrow band fixture with device soldered)

V_{DD}=28V I_{DQ}=100mA, CW

Freq(MHz)	Pin(dBm)	Pout(dBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
5000	37.70	48.08	64.27	4.03	10.38	56.96
5100	37.50	48.15	65.31	4.16	10.65	56.07
5200	37.70	48.25	66.83	4.38	10.55	54.50
5300	37.70	48.47	70.31	4.66	10.77	53.88
5400	36.60	48.57	71.94	4.78	11.97	53.75
5500	37.20	48.58	72.11	4.85	11.38	53.10
5600	38.1	48.47	70.31	4.75	10.37	52.86
5700	38	48.4	69.18	4.56	10.40	54.18
5800	36.6	48.36	68.55	4.39	11.76	55.77
5900	37.5	48.25	66.83	4.19	10.75	56.97
6000	37.5	47.86	61.09	3.81	10.36	57.27

Recommended driver: GTAH58008C6

Applications and Features

- Suitable for wireless communication infrastructure, wideband amplifier, EMC testing, ISM etc.
- High Efficiency and Linear Gain Operations
- Thermally Enhanced Industry Standard Package
- High Reliability Metallization Process
- Excellent thermal Stability and Excellent Ruggedness
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

1. Set VGS to the pinch--off (VP) voltage, typically –5 V
2. Turn on VDS to nominal supply voltage (28V)
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically –5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	150	Vdc
Gate--Source Voltage	V_{GS}	-10,+2	Vdc
Operating Voltage	V_{DD}	36	Vdc
Maximum Forward Gate Current @ TC = 25°C	Igmax	16	mA

Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature(See note 1)	T_J	+225	°C
Total Device Power Dissipation (Derated above 25°C, see note 2)	Pdiss	120	W

Note: 1. Continuous operation at maximum junction temperature will affect MTTF
2.Bias Conditions should also satisfy the following expression: Pdiss < (Tj – Tc) / RJC and Tc = Tcase

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T_C= 85°C, T_J=200°C, RF CW operation	$R_{\theta JC}$	1.5	C/W

Table 3. Electrical Characteristics (T_C = 25℃ unless otherwise noted)

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS}=-8V; I_{DS}=16mA	V_{DSS}	150			V
Gate Threshold Voltage	V_{DS} = 28V, I_D =16mA	V_{GS}(th)	-4		-2	V
Gate Quiescent Voltage	V_{DS} =28V, I_{DS}=100mA, Measured in Functional Test	$V_{GS(Q)}$		-2.35		V

Typical performance

5-6GHz

Figure 2: Small singal gain and return loss Vs Frequency

Vds=28V, Idq=100mA, input power=0dBm

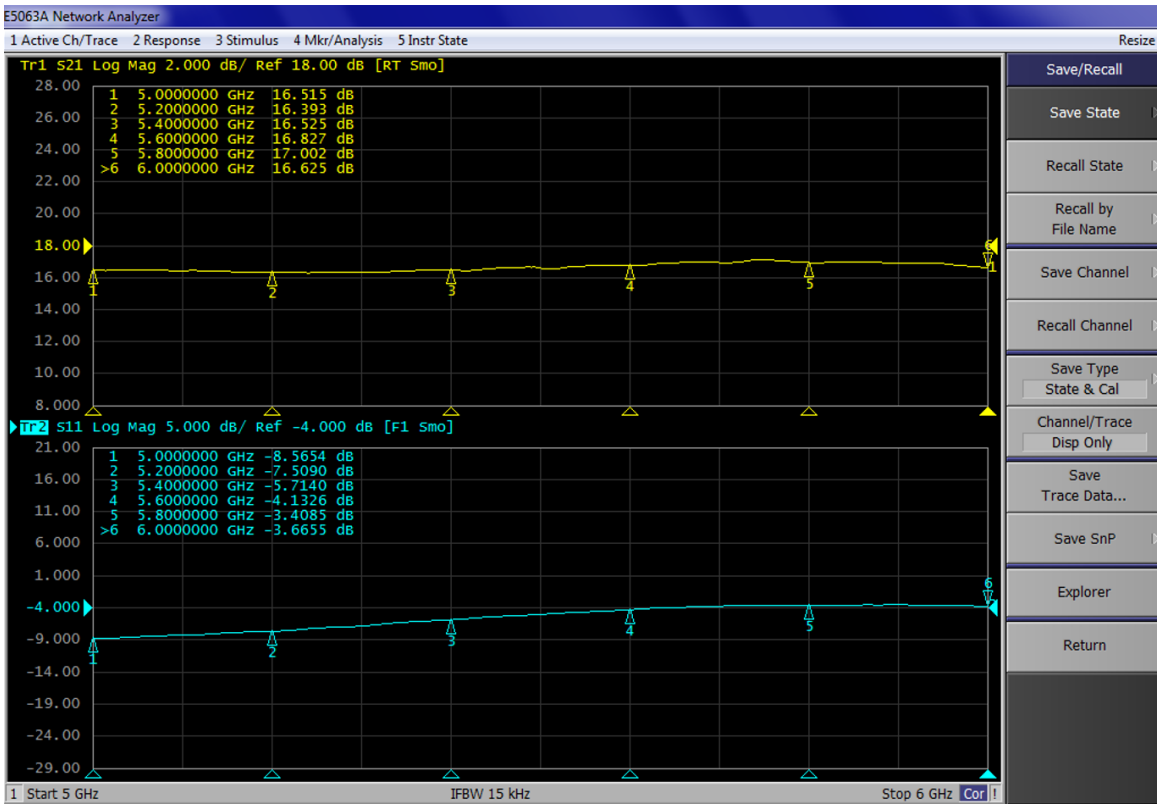
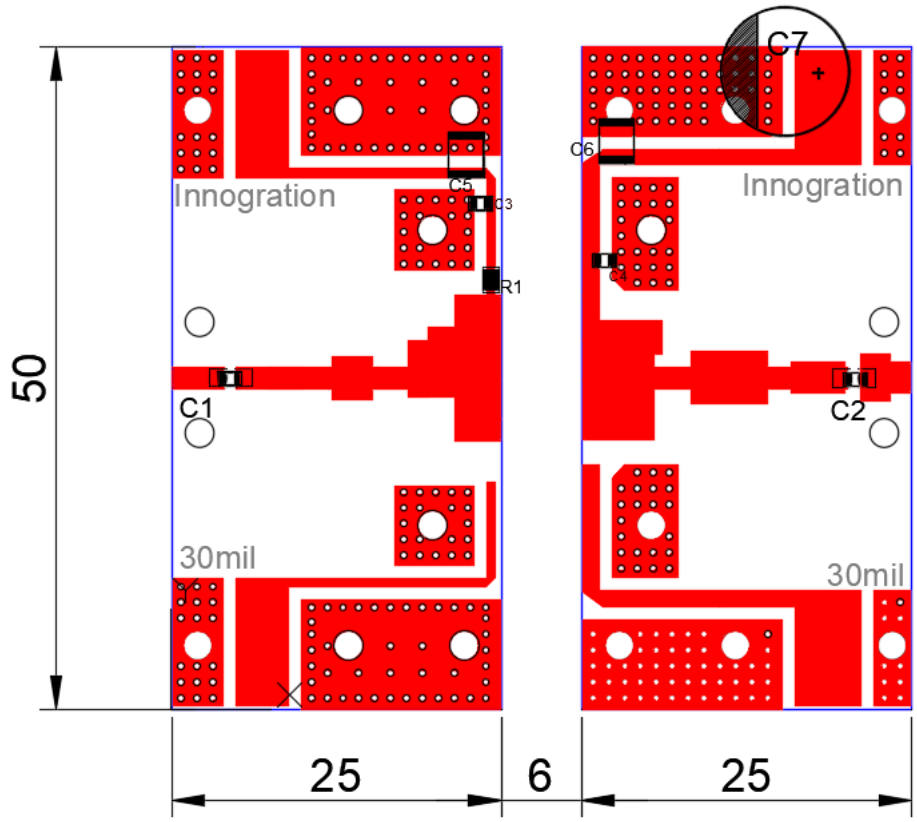


Figure 4: Picture and Bill of materials of 4.8-5.9GHz wide band application circuit

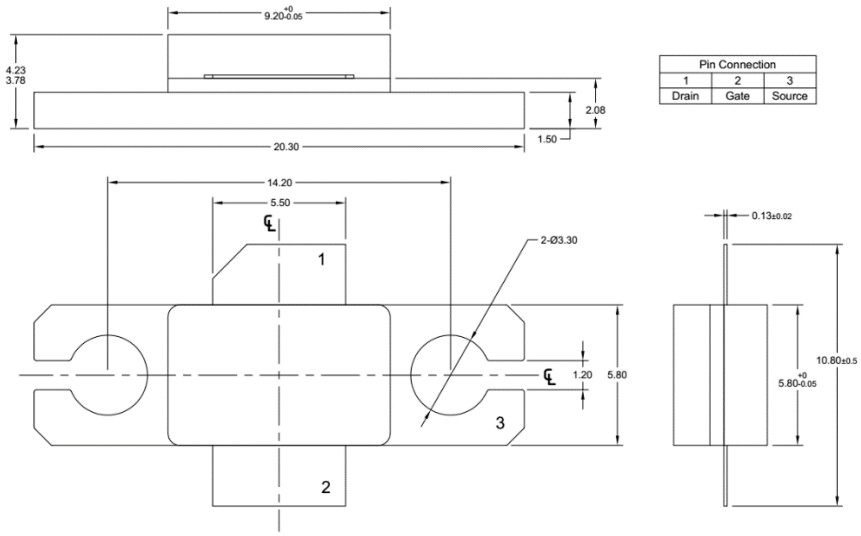
(Layout Gerber file upon request，20mils RO4350B)



Component	Description	Suggested Manufacturer
C7	470uF/63V	
C5,C6	10uF	10uF/100V
C1,C2, C3, C4	3.9pF(MQ300805)	BEIJING YUANLU HONGYUAN ELECTRONIC TECHNOLOGY CO., LTD
R1	Chip Resistor,10Ω	0603
PCB	30mil Rogers 4350B	

Package Outline

Flanged ceramic package; 2 leads



OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-GXB					10/10/2017

Figure 1. Package Outline PKG-G2E

Revision history

Table 5. Document revision history

Date	Revision	Datasheet Status
2025/2/18	**V1.0**	**Preliminary Datasheet Creation**

Application data based on YHG-25-02

Notice